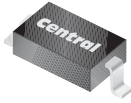


**CMDSH05-4**  
**SURFACE MOUNT**  
**LOW  $V_F$**   
**SILICON SCHOTTKY DIODE**



[www.centrasemi.com](http://www.centrasemi.com)

**SUPERmini™**



**SOD-323 CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMDSH05-4 is a 40 volt Schottky Diode packaged in a space saving surface mount SOD-323 case. This **SUPERmini™** device has been designed for applications requiring a low forward voltage drop.

**MARKING CODE: C55**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current, $t_p \leq 1.0\text{ms}$
Peak Forward Surge Current, $t_p = 8.0\text{ms}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
$V_{RRM}$	40	V
$I_F$	500	mA
$I_{FRM}$	3.5	A
$I_{FSM}$	10	A
$P_D$	250	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	500	$^\circ\text{C/W}$

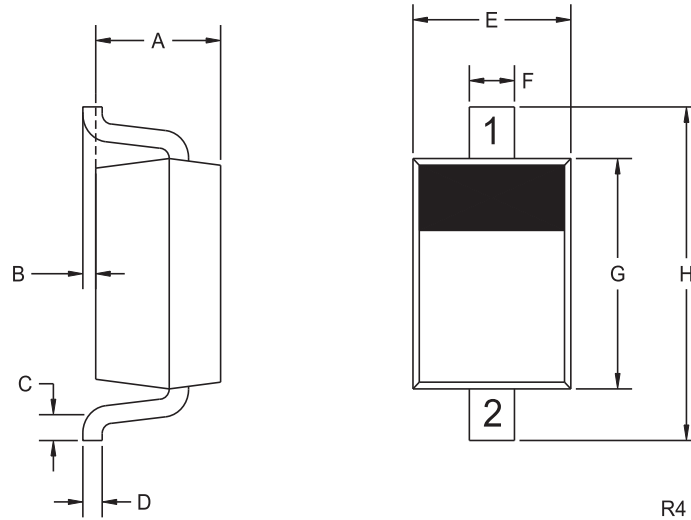
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=10\text{V}$			20	$\mu\text{A}$
$I_R$	$V_R=30\text{V}$		60	100	$\mu\text{A}$
$I_R$	$V_R=30\text{V}, T_A=85^\circ\text{C}$		2.5		mA
$I_R$	$V_R=30\text{V}, T_A=100^\circ\text{C}$		6.0		mA
$BV_R$	$I_R=500\mu\text{A}$	40			V
$V_F$	$I_F=100\mu\text{A}$			0.13	V
$V_F$	$I_F=1.0\text{mA}$			0.21	V
$V_F$	$I_F=10\text{mA}$			0.27	V
$V_F$	$I_F=100\text{mA}$			0.35	V
$V_F$	$I_F=500\text{mA}$			0.47	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$			50	pF

**CMDSH05-4**  
**SURFACE MOUNT**  
**LOW  $V_F$**   
**SILICON SCHOTTKY DIODE**



**SOD-323 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) CATHODE
- 2) ANODE

**MARKING CODE: C55**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R2 (2-November 2010)